

## Transparent UV-absorbers thin films of zinc oxide: Ceria system synthesized via sol-gel process

Juliana Fonseca de Lima, Renata Figueredo Martins, Osvaldo Antonio Serra\*

Department of Chemistry, FFCLRP, USP, Avenida Bandeirantes 3900, CEP 14040-901, Ribeirão Preto, SP, Brazil

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### ABSTRACT

Transparent nanostructure ZnO:CeO<sub>2</sub> and ZnO thin films to use as solar protector were prepared by non-alkoxide sol-gel process and deposited on boronsilicate glass substrate by dip-coating technique and then heated at 300–500 °C. The films were characterized structurally, morphologically and optically by X-ray diffraction (XRD), atomic force microscopy (AFM), field emission gun-scanning electron microscopy (FEG-SEM), scanning electron microscopy (SEM) and UV-Vis transmittance spectroscopy. The coatings presented high transparency in the visible region and excellent absorption in the UV. The band gap of the deposited films was estimated between 3.10 and 3.18 eV. Absorption of the films in the UV was increased by presence of cerium. The results suggest that the materials are promising candidates to use as coating solar protective.

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### 1. Introduction

The need to use UV absorbers, organics and inorganics, to protect material that has been exposed to the solar radiation has motivated numerous studies about the synthesis and properties of these absorbers. They have been most frequently used in cosmetics to prevent sunburns and skin cancer [1], in glass, polymers, and wooden substrates, maintaining the integrity of their physical-chemical properties.

Organic UV absorbers have been widely used as coatings to protect organic materials against UV radiation. UVA (benzophenones, anthranilates and dibenzoylmethanes) and UVB absorbers (PABA derivatives, salicylates, cinnamates and camphor derivatives) are utilized combined to cover the whole UVA/UVB range (290–400 nm) [2]. Their properties as light in weight, resistant to corrosion, relatively easily fabricated at moderate temperatures and low cost of the starting materials are the most important reasons for their wide utilization. However, their applications sometimes are limited due to their sensibility to heat and self photo-degradation leading to a low effective lifetime and the formation of another substances UV non-absorbers.

Inorganic materials have been extensively utilized in sunscreen products due to the efficient absorption in the UVA and UVB region. Inorganic or nonchemical sunscreen filters, titania (TiO<sub>2</sub>) and zinc oxide (ZnO) are effective inorganic sunscreens and commonly used nowadays [3–5]. The morphology of these compounds

is very important to determine the utilization of them as absorbers in the UVA and UVB region. For instance, amorphous ZnO and TiO<sub>2</sub> have a much higher band gap than the respective crystalline phases showing its absorption, displaced to lower wavelengths, does not cover the whole UV region of interest. Ceria (CeO<sub>2</sub>) has potential interest as an inorganic UV blocking material. Many studies have reported the synthesis of nano-sized particles of ceria undoped and doped for several applications [6–9]. Some of their properties as: being obtained as crystalline or amorphous forms at low temperatures with similar band gaps near to 3.1 eV (about 400 nm) [10]; refractive index of CeO<sub>2</sub> in the visible region is 2.1–2.2 [11], almost the same as that of ZnO (2.0–2.1) [12], become it a very attractive material to be utilized as UV absorbers.

Sol-gel methodology has been extensively used in order to synthesize inorganic materials, because it requires very simple equipments, allows the use of different precursors and soft conditions [13]; also the sol-gel method is a simple, low cost and large area coating method [14]. Some studies have been reported in obtaining UV absorber films used the sol-gel process, for example, in the synthesis of composites of TiO<sub>2</sub>-CeO<sub>2</sub>-SiO<sub>2</sub> and CeO<sub>2</sub>-SiO<sub>2</sub> [15], silica-coated TiO<sub>2</sub> [16]. However, none of these studies relate the synthesis and characterization of composites of the ZnO:CeO<sub>2</sub> using the sol-gel process for applications as UV filter for coatings. The system ZnO:CeO<sub>2</sub> become a potential UV absorber with desired properties as wide band gap, optical transparency in the visible region, transparent coating in high temperature and good heat resistance. These good properties allow to apply the ZnO:CeO<sub>2</sub> in optical materials [14,15]. In this study, ZnO:CeO<sub>2</sub> films have been synthesized by the sol-gel process using non-alkoxide route [17].

\* Corresponding author. Tel.: +55 16 3602 3746.

E-mail address: [osaserra@usp.br](mailto:osaserra@usp.br) (O.A. Serra).

## 2. Experimental procedures

In this experiment, a similar procedure as described in [18,19] is performed. Zinc acetate dihydrate and cerium nitrate are used as starting materials sources, ethanol and lactic acid were used as solvent and stabilizer, respectively. Zinc acetate dihydrate was added to ethanol ( $[Zn^{2+}] = 0.44 \text{ mol L}^{-1}$ ) and later mixed with an ethanolic solution of cerium nitrate ( $0.10 \text{ mol L}^{-1}$ ) in appropriated stoichiometry ( $Zn^{2+}:Ce^{3+} = 9:1$ ). The solution was heated under reflux for 3 h at  $70^\circ\text{C}$  with additions of lactic acid to stabilize the sol, the flask was fitted with a condenser and a trap ( $CaCl_2$ ) to avoid moisture exposure. Stable and translucent colloidal precursor sol has been obtained. The films were deposited over borosilicate glass substrates previously cleaned with a sodium dodecylsulfate detergent, treated ultrasonically with deionized water for 30 min [20]. Transfer process onto glass substrates was carried out by dip-coating at  $4.0 \text{ cm min}^{-1}$  with a short immersion time (30 s). The films were then annealed to temperatures of 300, 400 and  $500^\circ\text{C}$  during 15 min. The coating procedure was repeated five times to each temperature. ZnO films were obtained utilizing the same procedure as described previously. In Fig. 1 are the final films ZnO ( $500^\circ\text{C}$ ) and ZnO:CeO<sub>2</sub> ( $500^\circ\text{C}$ ), the coatings show very high transparency.

The sample crystallographic characterization was performed by X-ray diffraction (XRD) in a Siemens D5000 diffractometer equipped with Cu K $\alpha$  radiation. ZnO and ZnO:CeO<sub>2</sub> crystallite size was determined by Scherrer equation [21]. The UV absorption capacity of the films was analyzed by absorption spectra from 280 to 700 nm that were measured in a spectrometer HP 8453 Diode Array. The morphologies and cross-sections were investigated respectively by field emission gun-scanning electron microscopy (FEG-SEM) on a Quanta 200 FEG – FEelectron microscopy that were performed in the Center of Microscopy at Universidade Federal de Minas Gerais, Belo Horizonte, MG, Brazil (<http://www.microscopia.ufmg.br>), and a scanning electron microscopy (SEM) on a Scanning Electron Microscope Zeiss EVO 50. The surface roughness and also morphology of ZnO:CeO<sub>2</sub> ( $500^\circ\text{C}$ ) were measured with a Nanoscope III atomic force microscope (Digital Co. Instruments, USA) using a normal silicon nitride tip ( $X_{\mu\text{m}}$ ) in Tapping Mode scanning the surface with an oscillating tip to its resonant frequency (200–400 kHz).

## 3. Results and discussion

In Fig. 2 is the XRD pattern of the film calcined at  $500^\circ\text{C}$ . The interplanar distances observed are related to the CeO<sub>2</sub> phases, fluo-

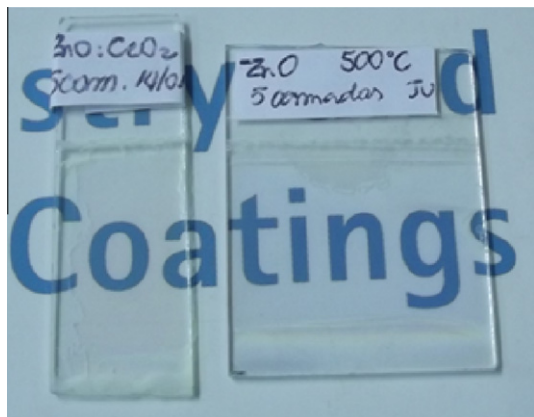


Fig. 1. Photography of the transparent films with five layers and treated at  $500^\circ\text{C}$ . (1) ZnO:CeO<sub>2</sub> and (2) ZnO.

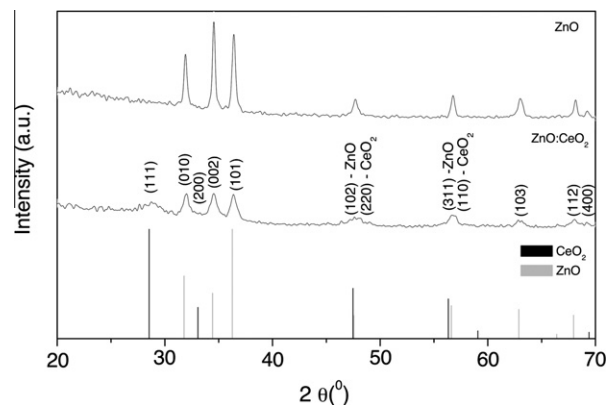


Fig. 2. X-ray diffraction patterns of ZnO and ZnO:CeO<sub>2</sub> films annealed at  $500^\circ\text{C}$ .

rite-type, face-centered cubic unit cell and space group Fm3m (225) or ZnO phases, hexagonal system, primitive unit cell and space group P63mc (186) [22], however the display peaks for the ZnO is sharper, once CeO<sub>2</sub> is presented in the range of 10%.

The average crystallite size of the particles on the films was calculated by Scherrer's Formula [21] and the estimated values are in Table 1. The average crystallite sizes for ZnO and ZnO:CeO<sub>2</sub> were 25.1 and 19.8 nm. The average crystallite sizes show a minimal decrease with cerium presence.

Fig. 3 shows the UV–Vis spectra of the films of ZnO. The films thermally treated at 400 and  $500^\circ\text{C}$  presented high absorption in the 290–400 nm region and good transparency in the visible (400–700 nm), while the obtained at  $300^\circ\text{C}$  presented very low UV absorption because in this case does not happen the formation of zinc oxide. The UV absorption increased linearly with the thickness of the films obtained by dip-coating process. The films treated at  $500^\circ\text{C}$  presented a more intense absorption between 300 and 400 nm due to a higher crystallinity of the ZnO phase, as showed in the XRD patterns, Fig. 2.

The ZnO:CeO<sub>2</sub> thin films treated at 300, 400 and  $500^\circ\text{C}$ , exhibit efficient absorption in the 290–400 nm region and a good transparency in the visible (400–700 nm), with a negligible yellowish coloration from the CeO<sub>2</sub> (Fig. 4). As observed for the ZnO, the absorption increased with the thickness and the temperature treatment of the films. Due to the formation of crystalline phase of CeO<sub>2</sub> at low temperature ( $300^\circ\text{C}$ ), the films of the composites ZnO:CeO<sub>2</sub> present high absorption even at  $300^\circ\text{C}$ . The presence of CeO<sub>2</sub> imply in higher absorption in the 290–400 nm region than the films containing only ZnO (Figs. 3 and 4).

The good transmission in the visible region and good absorption in the UV region corresponds to the ideal band gap of the films. The Tauc Plot [23] is commonly used to determine the optical band gap in thin film materials by the following equation:

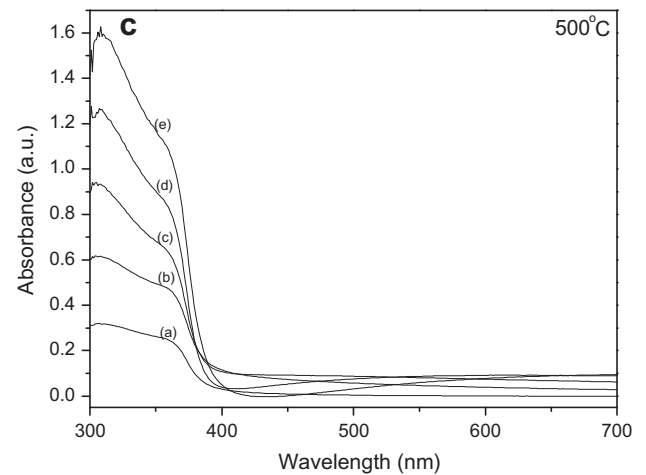
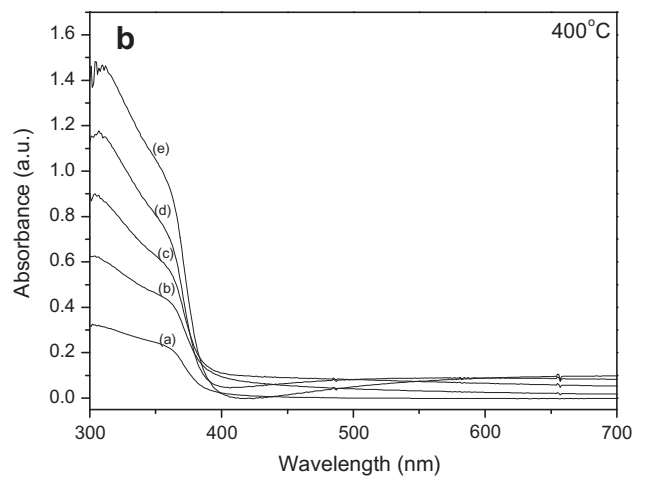
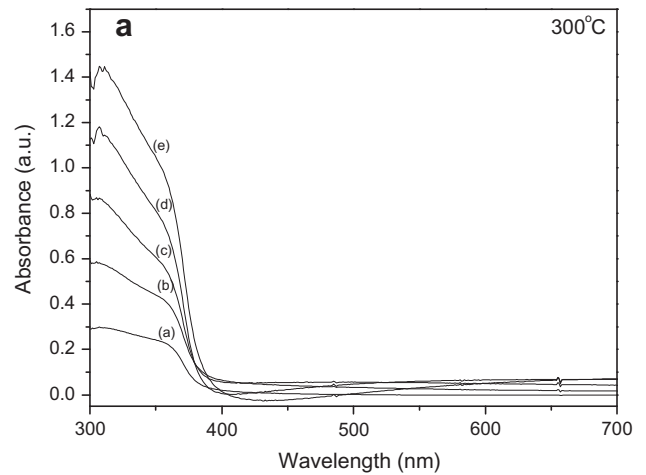
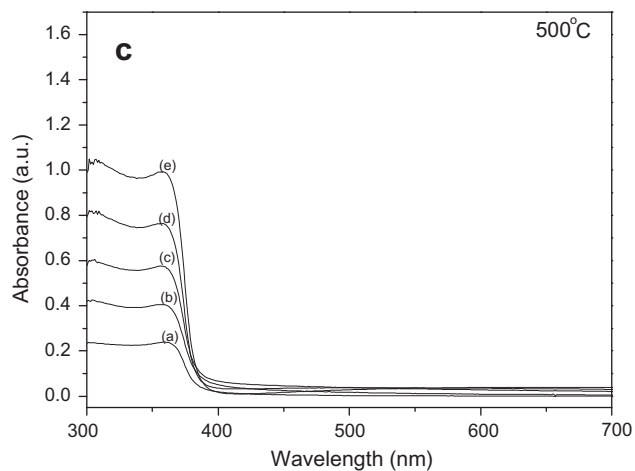
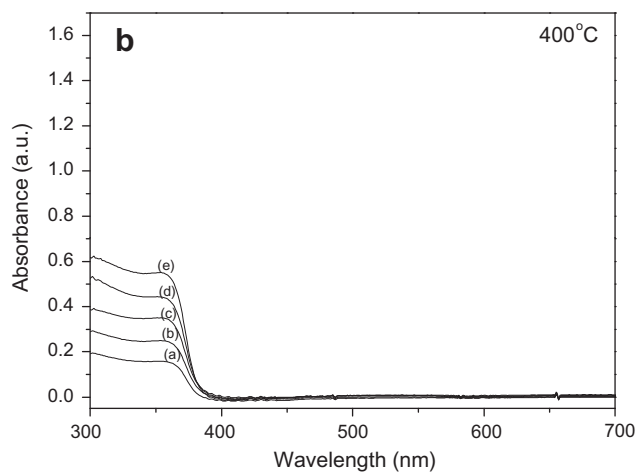
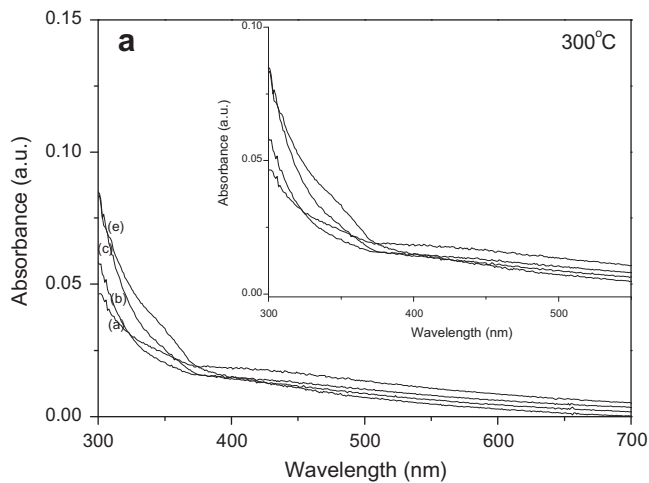
$$(\alpha hv) = A(hv - E_g)^n \quad (1)$$

where  $\alpha$  is the absorption coefficient,  $hv$  is the photon energy and  $E_g$  is the optical band gap. The optical absorption coefficient  $\alpha$  can be calculated from the equation:

$$\alpha d = \ln(1/T) \quad (2)$$

where  $T$  is the transmittance and  $d$  is the thickness of the films.

The optical band gap was estimated by extrapolating the straight line region in the plot of  $(\alpha hv)^2$  versus photon energy (Fig. 5), the extrapolated band gap values are 3.10 and 3.18 for ZnO:CeO<sub>2</sub> and ZnO films respectively, these values have relevance in solar protection.



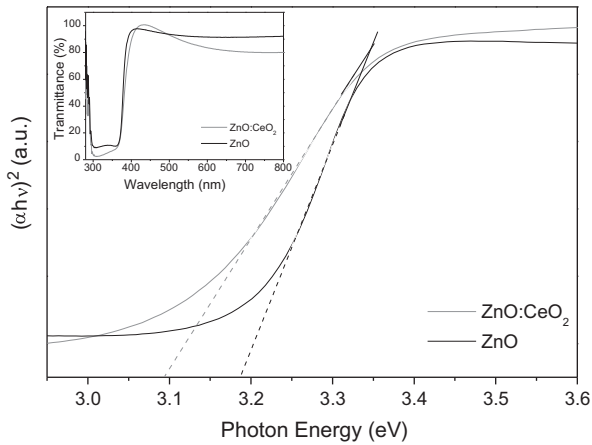
**Fig. 3.** Absorption spectra of ZnO films annealed at 300, 400 and 500 °C: (a) 1 layer, (b) 2 layers, (c) 3 layers, (d) 4 layers and (e) 5 layers.

**Fig. 4.** Absorption spectra of ZnO:CeO<sub>2</sub> films annealed at 300, 400 and 500 °C: (a) 1 layer, (b) 2 layers, (c) 3 layers, (d) 4 layers and (e) 5 layers.

FEG-SEM images in Fig. 6a and b and show the morphological aspects of the thin films ZnO and ZnO:CeO<sub>2</sub> on the surface of the substrate. The deposited films have a granular structure with a size of about 25 nm for ZnO film forming small aggregates (Fig. 6a) and for ZnO:CeO<sub>2</sub> film the particles size have about 50–100 nm for CeO<sub>2</sub> agglomerate that is the white part of the image (Fig. 6b) and it is possible to observe that small particles of ZnO form agglomerates of approximately 125 nm (Fig. 6b). Comparing the particle size to the crystallite size (calculated by X-ray diffraction)

for ZnO:CeO<sub>2</sub>, it is possible to note a difference in the values due to the formation of nanocrystallite aggregates [24] or agglomerates [24]. It is noteworthy to say that the size of both crystallites and particles are not necessarily the same since the latter may be formed by a number of the former [25].

SEM was used to obtain images to determine, even approximately, the thickness of the films in order to obtain such images was made a cross-section in the substrate. Photomicrographs for the ZnO and ZnO:CeO<sub>2</sub> films with five layers and thermally treated



**Fig. 5.** Plot of  $(\alpha hv)^2$  versus photon energy and optical transmittance spectra (inside) for ZnO and ZnO:CeO<sub>2</sub> thin films heated at 500 °C.

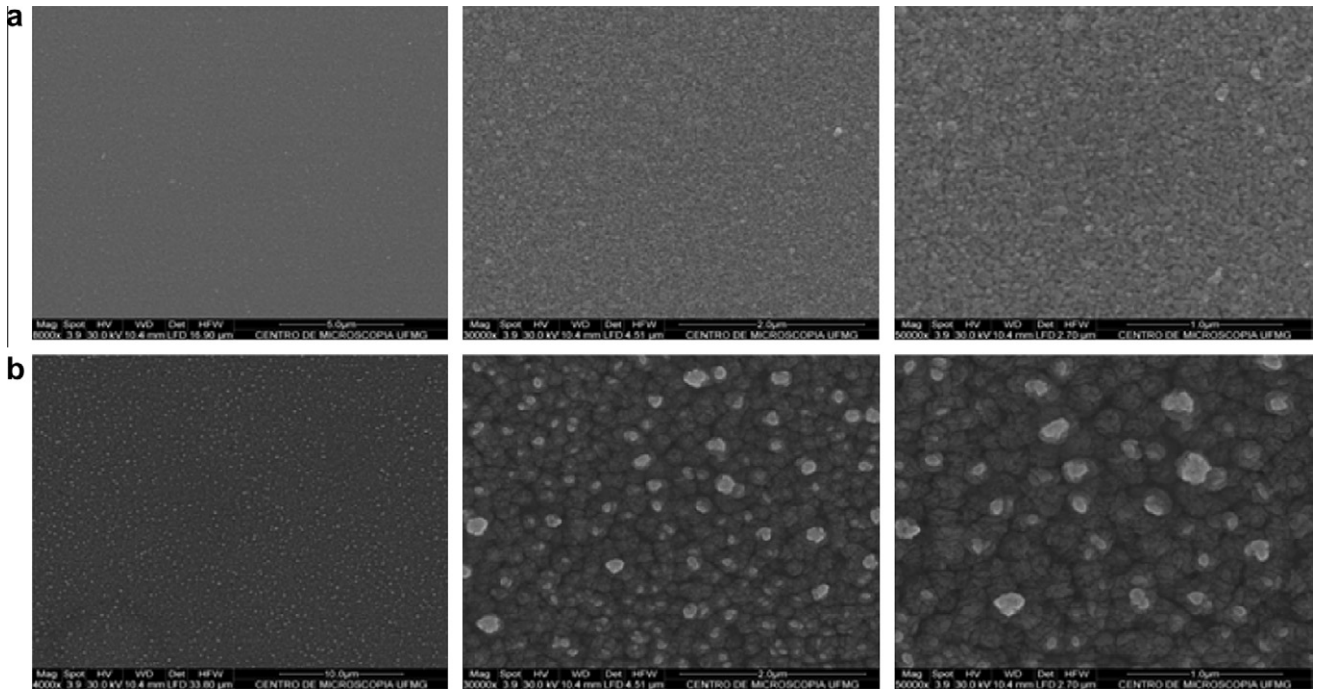
at 500 °C are shown in Figs. 7a and b. It is observed that the film consists of five layers of ZnO and has a thickness of 126–178 nm

(Fig. 7a) and the film formed by the system ZnO:CeO<sub>2</sub> has a thickness of 270–267 nm (Fig. 7b).

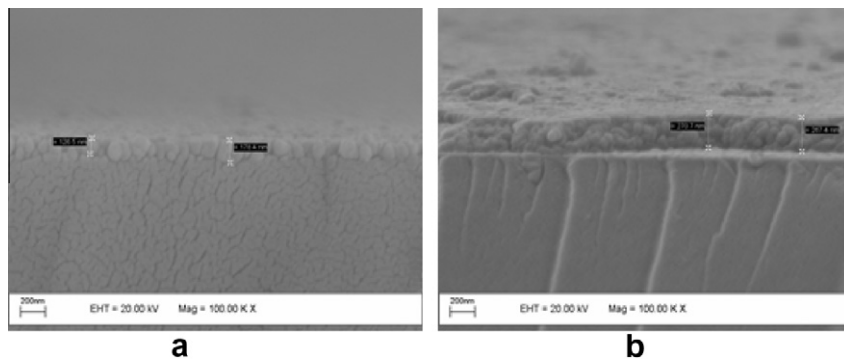
The 2D and 3D surface topographies of interested film ZnO:CeO<sub>2</sub> treated at 500 °C obtained by AFM are illustrated in Fig. 8. The films have relatively spherical grains with nanometric dimensions, dense structure and no cracks. In Fig. 8b is shown the difference in roughness that is low. The presence of “mountains” of different sizes is due probably to the formation of two oxides that constitute the studied system, ZnO and CeO<sub>2</sub>.

#### 4. Conclusions

ZnO and ZnO:CeO<sub>2</sub> thin films were successfully prepared by non-alkoxide sol-gel method, a simple and low cost method, and deposited on glass substrate by dip-coating. The film thickness could be controlled by the coatings conditions and the solution viscosity. During the synthesis process a stable and translucent colloidal precursor sol was obtained, after transfer process onto glass substrate, transparent films with high UV absorption were obtained and the presence of cerium increased the capacity of the films in absorber the UV range.

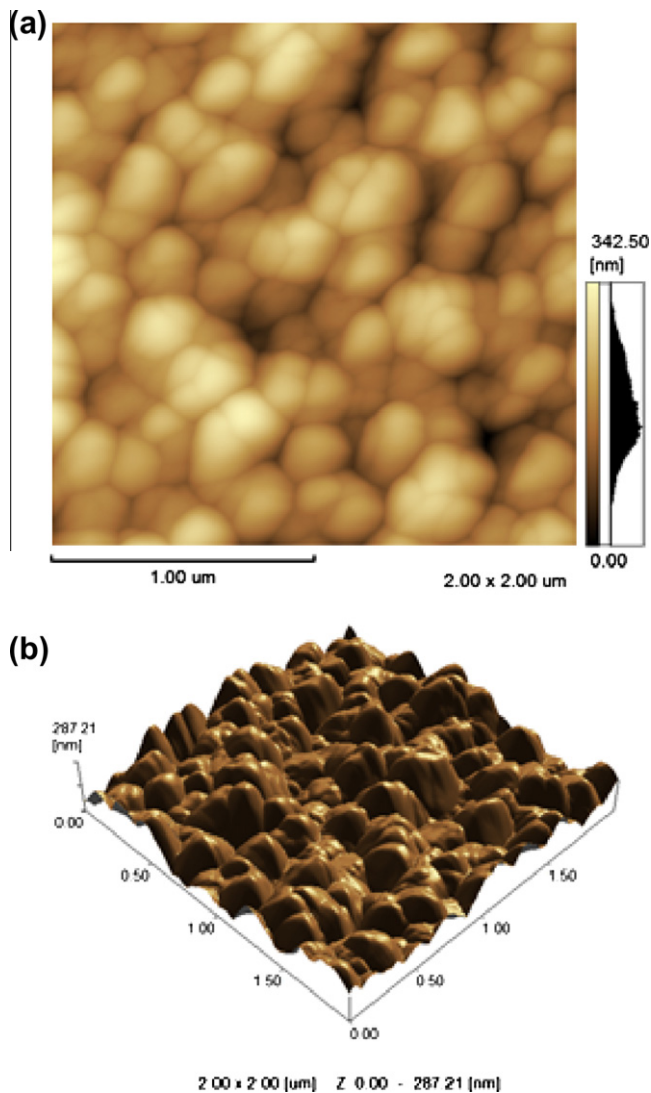


**Fig. 6.** FEG-SEM images of the surface thin films. (a) FEG-SEM images of ZnO thin film heated at 500 °C. (b) FEG-SEM images of ZnO:CeO<sub>2</sub> thin film heated at 500 °C.



**Fig. 7.** SEM images of cross-section of the films heated at 500 °C: (a) ZnO and (b) ZnO:CeO<sub>2</sub>.





**Fig. 8.** AFM images of ZnO:CeO<sub>2</sub> thin film treated at 500 °C: (a) 2D image and (b) 3D image.

The final deposited thin films heated at 500 °C were chosen to finish the main analysis. Morphological characterizations showed the formation of nanostructured films with spherical grains, low roughness and no cracks. The band gap values observed for the

films were from 3.10 to 3.18 eV and it can be correlated with the nanocrystalline structure of the films and these values also allow the application in solar protection. The results suggest that the materials are promising candidates to use as coating solar protective.

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